

## N-Channel 60 V (D-S) Super Junction Power MOSFET

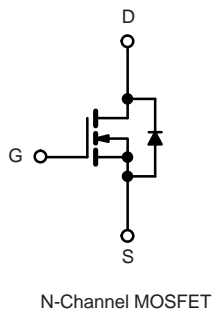
PRODUCT SUMMARY		
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>
60	0.0021 at V <sub>GS</sub> = 10 V	190
	0.0029 at V <sub>GS</sub> = 4.5 V	150

### FEATURES

- 175 °C Junction Temperature
- DT-Trench Power MOSFET
- Material categorization:



**RoHS**  
COMPLIANT



ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Gate-Source Voltage		V <sub>GS</sub>	± 20	V
Continuous Drain Current (T <sub>J</sub> = 175 °C) <sup>b</sup>	T <sub>C</sub> = 25 °C	I <sub>D</sub>	190	A
	T <sub>C</sub> = 100 °C		150 <sup>a</sup>	
Pulsed Drain Current		I <sub>DM</sub>	660	
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	190 <sup>a</sup>	
Avalanche Current		I <sub>AS</sub>	189	
Single Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E <sub>AS</sub>	750	mJ
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	235	W
	T <sub>C</sub> = 75 °C		157	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 10 sec	R <sub>thJA</sub>	10	15	°C/W
	Steady State		30	40	
Maximum Junction-to-Case		R <sub>thJC</sub>	0.55	1.0	

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. t ≤ 10 s.

**SPECIFICATIONS** ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

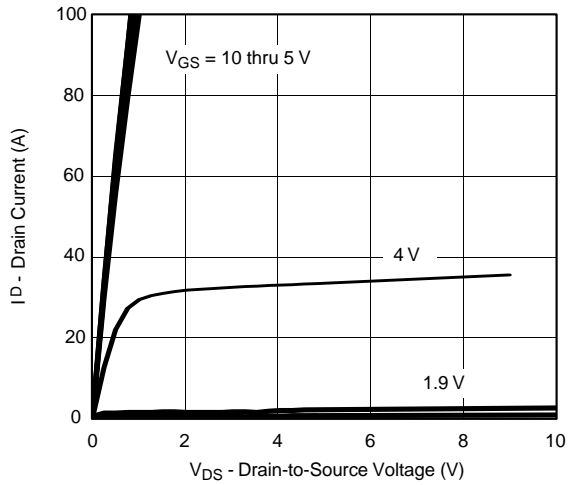
Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		2.5	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 48\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 48\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 48\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$			250	
On-State Drain Current <sup>b</sup>	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	190			A
Drain-Source On-State Resistance <sup>b</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		0.0021	0.0029	$\Omega$
		$V_{GS} = 10\text{ V}, I_D = 20\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.0027	0.0032	
		$V_{GS} = 10\text{ V}, I_D = 10\text{ A}, T_J = 175\text{ }^\circ\text{C}$		0.0030	0.0036	
		$V_{GS} = 4.5\text{ V}, I_D = 15\text{ A}$		0.0029	0.0039	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 48\text{ V}, I_D = 20\text{ A}$		45		S
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 48\text{ V}, f = 1\text{ MHz}$		8510		$\mu\text{F}$
Output Capacitance	$C_{oss}$			1070		
Reverse Transfer Capacitance	$C_{rss}$			95		
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{DS} = 48\text{ V}, V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		65	77	nC
Gate-Source Charge <sup>c</sup>	$Q_{gs}$			10		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			6.5		
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 48\text{ V}, R_L = 0.6\text{ }\Omega$ $I_D \cong 20\text{ A}, V_{GEN} = 10\text{ V}, R_g = 2.5\text{ }\Omega$		9		ns
Rise Time <sup>c</sup>	$t_r$			5		
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$			52		
Fall Time <sup>c</sup>	$t_f$			11		
<b>Source-Drain Diode Ratings and Characteristics</b> ( $T_C = 25\text{ }^\circ\text{C}$ )						
Pulsed Current	$I_{SM}$				660	A
Diode Forward Voltage	$V_{SD}$	$I_F = 20\text{ A}, V_{GS} = 0\text{ V}$		1	1.2	V
Reverse Recovery Time	$t_{rr}$	$I_F = 20\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		43	100	ns

**Notes:**

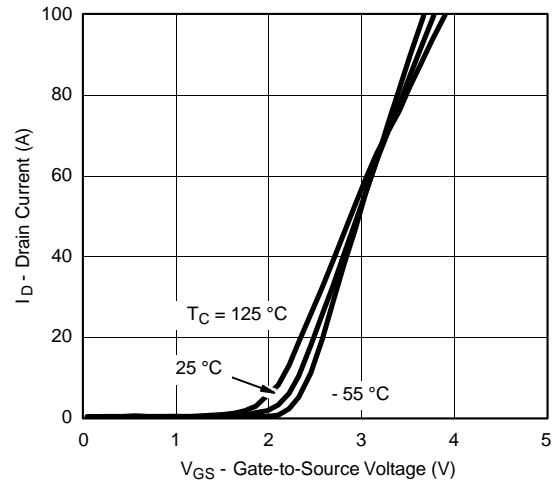
- For design aid only; not subject to production testing.
- Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

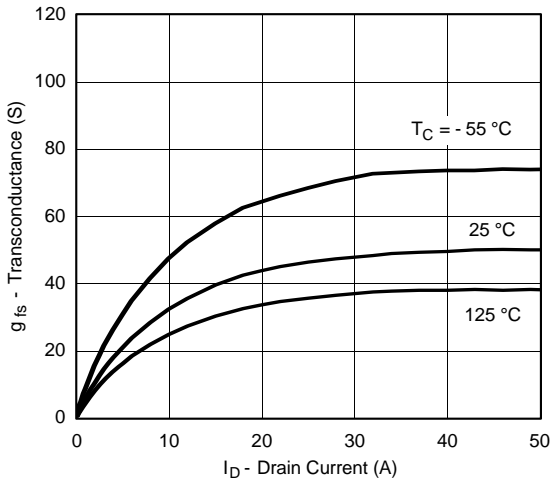
**TYPICAL CHARACTERISTICS** (25 °C unless noted)



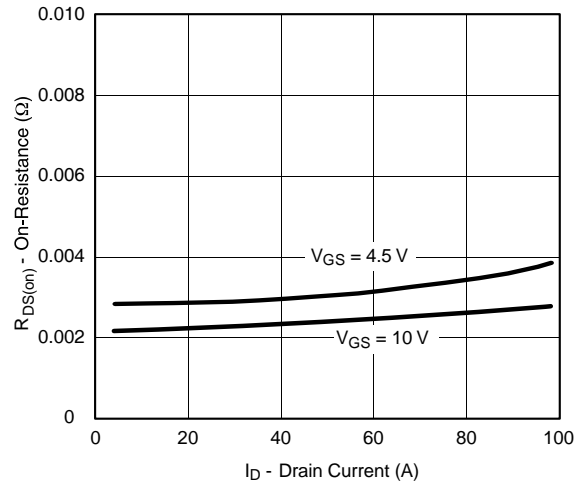
**Output Characteristics**



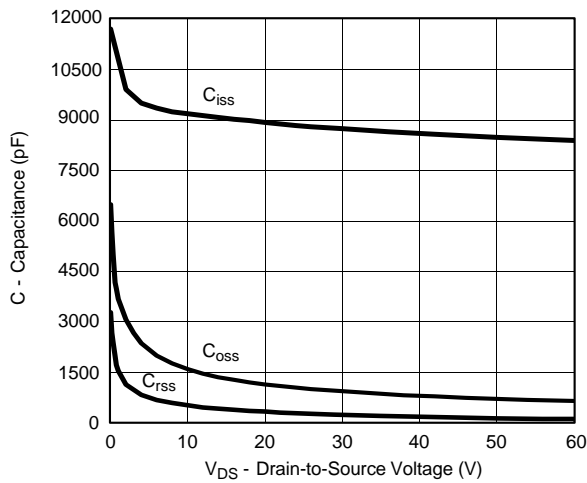
**Transfer Characteristics**



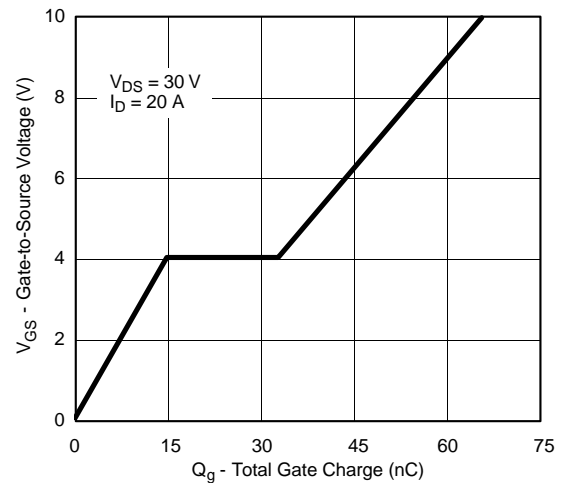
**Transconductance**



**On-Resistance vs. Drain Current**

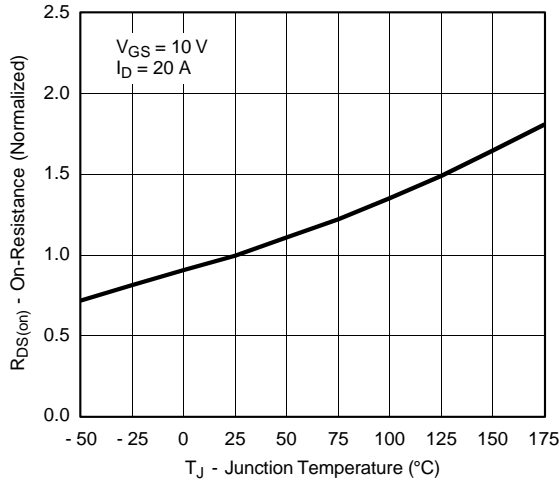


**Capacitance**

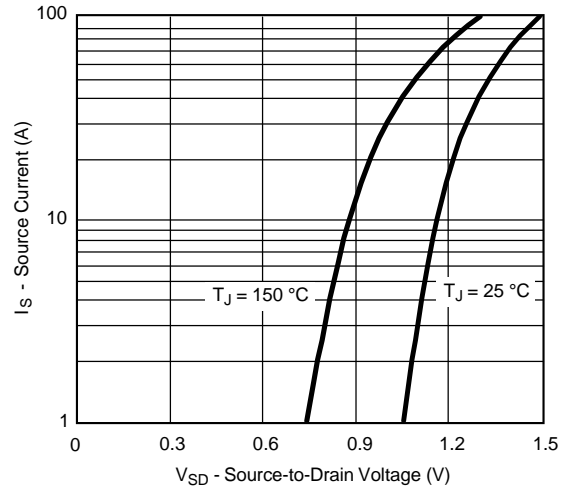


**Gate Charge**

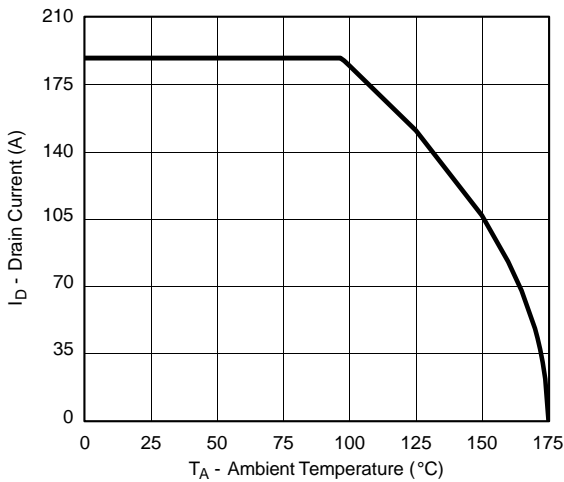
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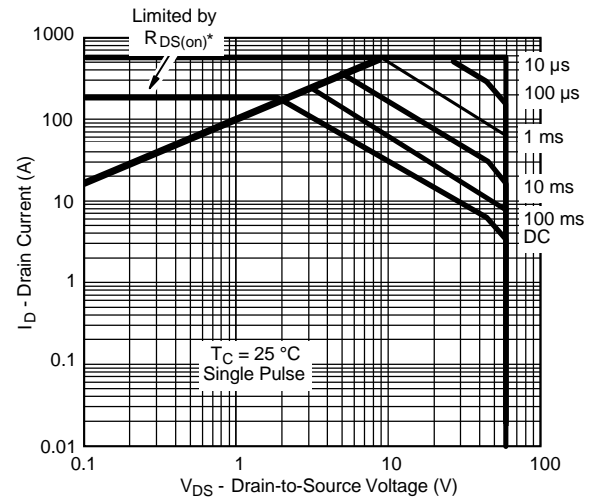
**On-Resistance vs. Junction Temperature**



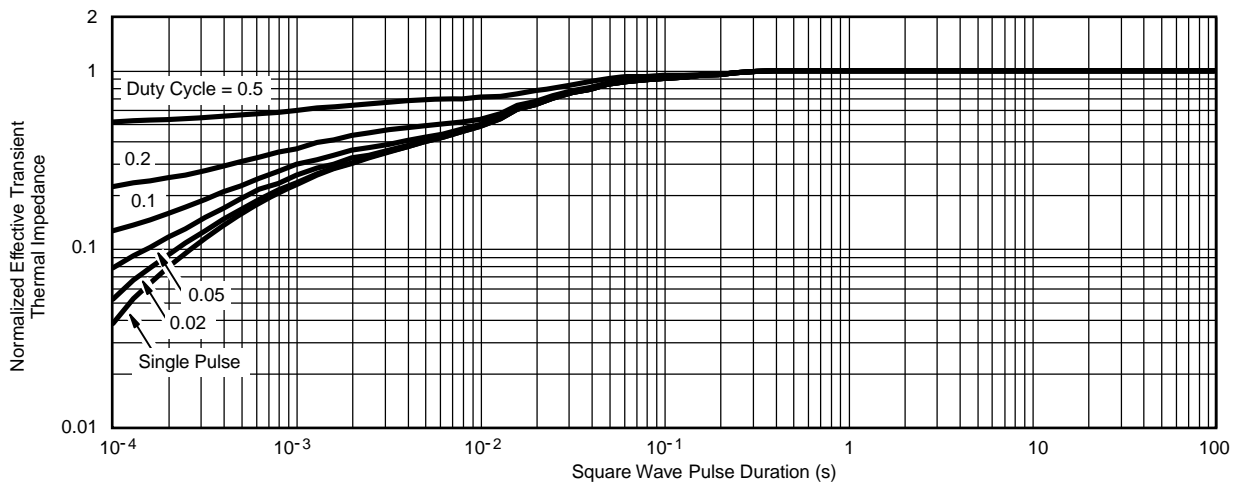
**Source-Drain Diode Forward Voltage**



**Maximum Drain Current vs. Ambient Temperature**

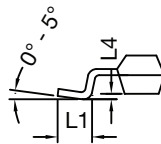
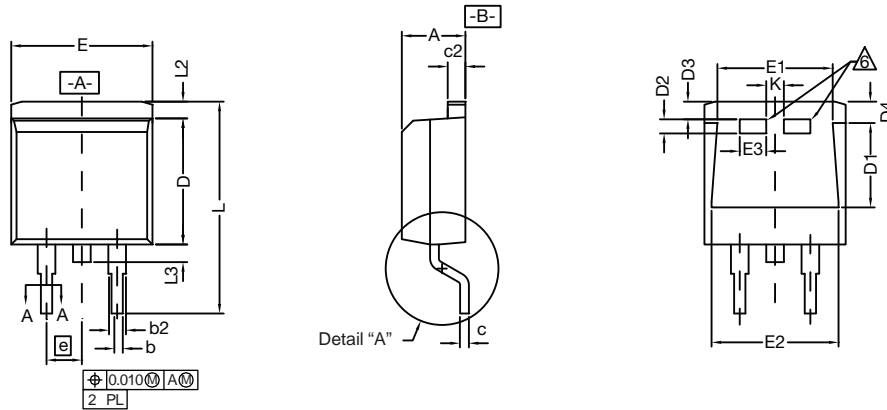


**Safe Operating Area**

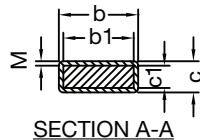


**Normalized Thermal Transient Impedance, Junction-to-Case**

## TO-263 (D<sup>2</sup>PAK): 3-LEAD



DETAIL A (ROTATED 90°)

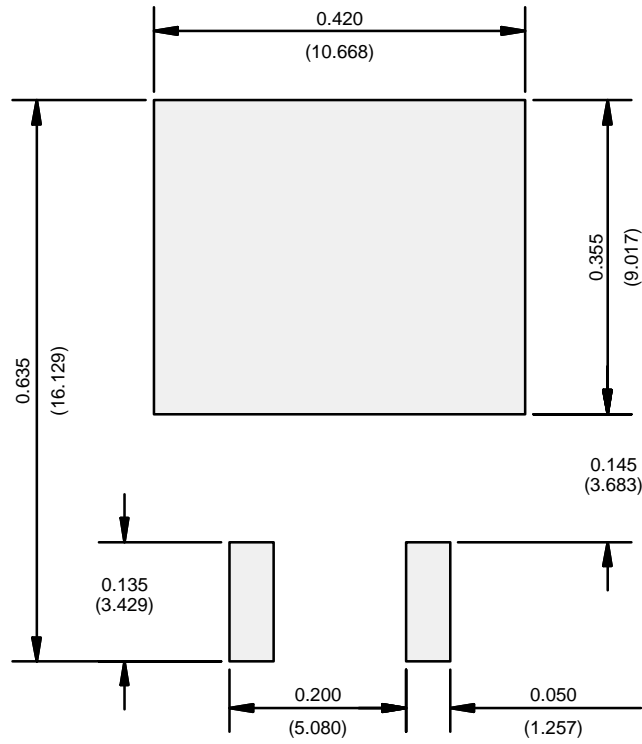


DIM.	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	0.160	0.190	4.064	4.826	
b	0.020	0.039	0.508	0.990	
b1	0.020	0.035	0.508	0.889	
b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
	Thick lead	0.023	0.027	0.584	0.685
c2	0.045	0.055	1.143	1.397	
D	0.340	0.380	8.636	9.652	
D1	0.220	0.240	5.588	6.096	
D2	0.038	0.042	0.965	1.067	
D3	0.045	0.055	1.143	1.397	
D4	0.044	0.052	1.118	1.321	
E	0.380	0.410	9.652	10.414	
E1	0.245	-	6.223	-	
E2	0.355	0.375	9.017	9.525	
<b>E3</b>	0.072	0.078	1.829	1.981	
e	0.100 BSC		2.54 BSC		
K	0.045	0.055	1.143	1.397	
L	0.575	0.625	14.605	15.875	
L1	0.090	0.110	2.286	2.794	
L2	0.040	0.055	1.016	1.397	
L3	0.050	0.070	1.270	1.778	
L4	0.010 BSC		0.254 BSC		
M	-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13					
DWG: 5843					

**Notes**

1. Plane B includes maximum features of heat sink tab and plastic.
2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
3. Pin-to-pin coplanarity max. 4 mils.
4. \*: Thin lead is for SUB, SYB.  
Thick lead is for SUM, SYM, SQM.
5. Use inches as the primary measurement.
6. This feature is for thick lead.

**RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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